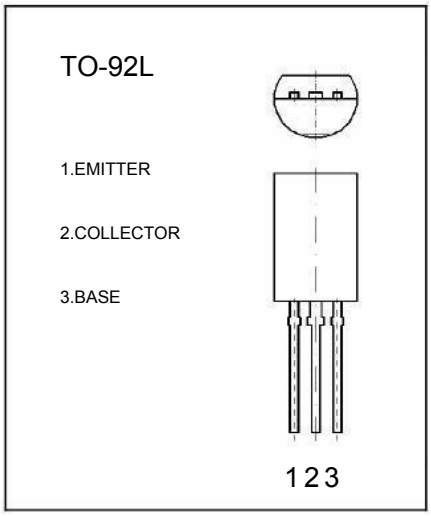
TO-92L Plastic-Encapsulate Transistors

C2482 TRANSISTOR (NPN)



FEATURES

Low collector to emitter saturation voltage $V_{CE(sat)}$.

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter			Units
V_{CBO}	Collector-Base Voltage		300	V
V_{CEO}	Collector-Emitter Voltage		300	V
V_{EBO}	Emitter-Base Voltage	7		V
I_C	Collector Current –Continuous	0.1		A
P_C	Collector Power Dissipation	0.9		W
T_J	Junction Temperature	150		℃
T_{stg}	Storage Temperature	-55-150		℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=3mA, I_B=0	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= 100μA, I_C=0	7			V
Collector cut-off current	I_{CEO}	V_{CE}=240V, I_B=0			1.0	μA
Collector cut-off current	I_{CBO}	V_{CB}=220V, I_E=0			5.0	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 7V， I_C=0			1.0	μA
DC current gain	$h_{FE(1)}$	V_{CE}=10V, I_C=20mA	30		150	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=10mA, I_B=1mA			1.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=10mA, I_B=1mA			1.0	V
Transition frequency	f_T	V_{CE}=10V, I_C=20mA f=30MHz	50			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	30-90	90-150